

## FORM PTO-1449

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H0004489  
(1139.1133101)Serial No.:  
10/697,660

**LIST OF PATENTS AND PUBLICATIONS**  
**APPLICANT'S INFORMATION**  
**DISCLOSURE STATEMENT**

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Filing Date:

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Group Art:

unknown 1765

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Examiner Initial	Document No.	Date	Name	Class	Sub Class	Filing Date If Appropriate
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ful	5,216,263	06/01/1993	Paoli			
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jl	5,412,678	05/02/1995	Treat et al.			
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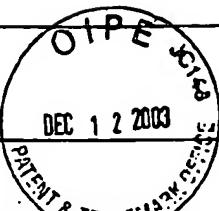
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BL	5,625,729	04/29/1997	Brown			
	5,642,376	06/24/1997	Olbright et al.			
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Al	6,154,480	11/28/2000	Magnusson et al.			

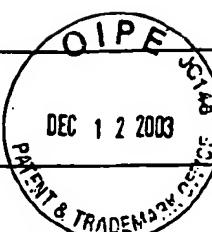
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<i>jl</i>	6,493,371	12/10/2002	Boucart et al.			

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dl	6,493,372	12/10/2002	Boucart et al.			
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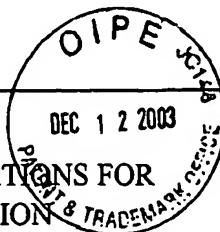
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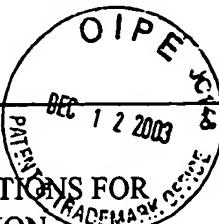
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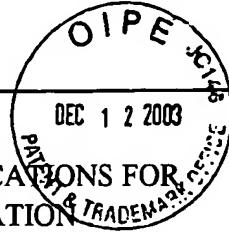
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<table border="1"> <tr> <td colspan="2">Applicant:</td> </tr> <tr> <td>Filing Date:</td> <td>Group Art:</td> </tr> <tr> <td>October 29, 2003</td> <td><del>unknown 1761</del></td> </tr> </table>				Applicant:		Filing Date:	Group Art:	October 29, 2003	<del>unknown 1761</del>
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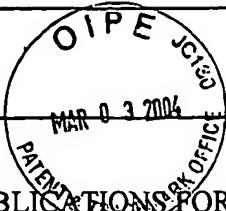
EXAMINER: *jl*

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Applicant: James R. Biard et al.

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Examiner Initial	Document No.	Date	Name	Class	Sub Class	Filing Date If Appropriate

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